



#### Product Summary

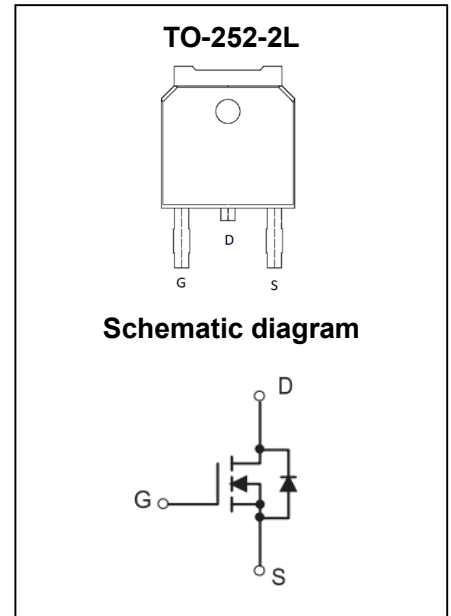
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	17m $\Omega$ @10V	40A
	26m $\Omega$ @4.5V	

#### Feature

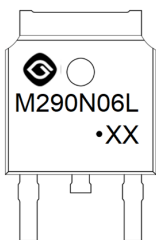
- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested
- 100%  $\Delta V_{DS}$  Tested

#### Application

- Power Switching Application



#### MARKING:



M290N06L = Device Code  
 XX = Date Code  
 Solid Dot = Green Indicator

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	60	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$I_D$	40	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	160	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	20	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	100	mJ
Power Dissipation <sup>5</sup>	$P_D$	60	W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	2.1	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

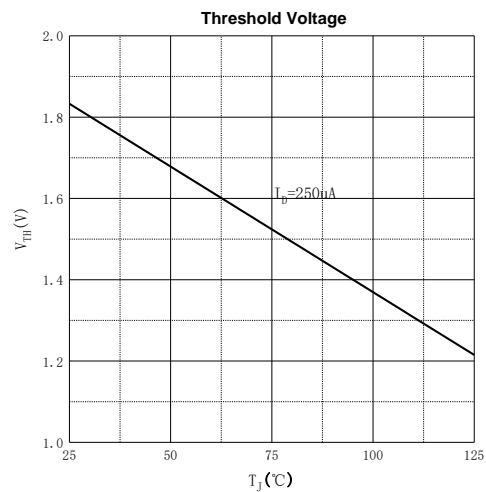
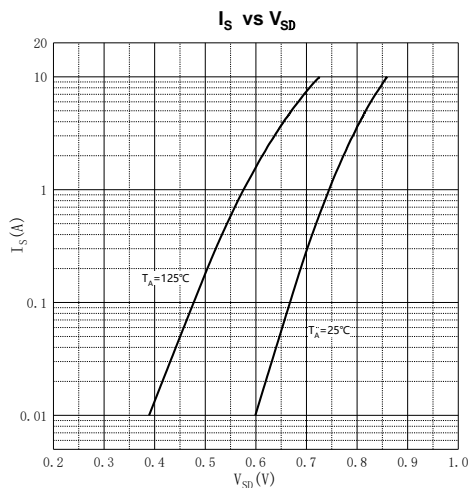
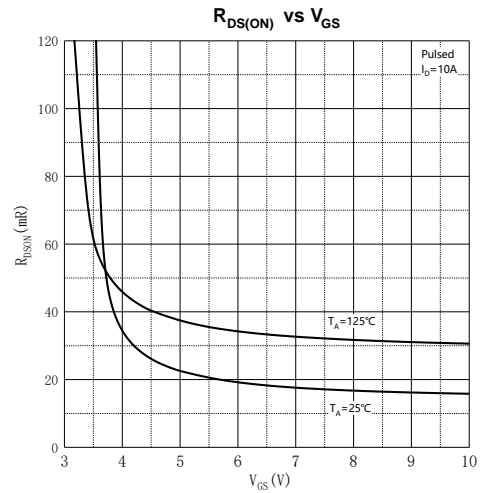
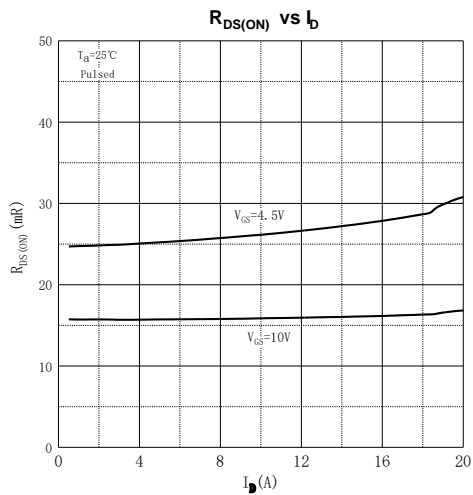
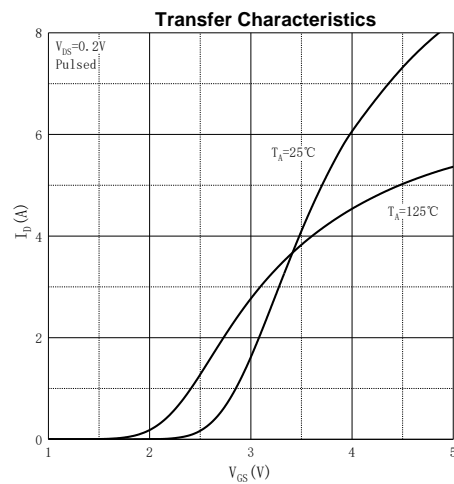
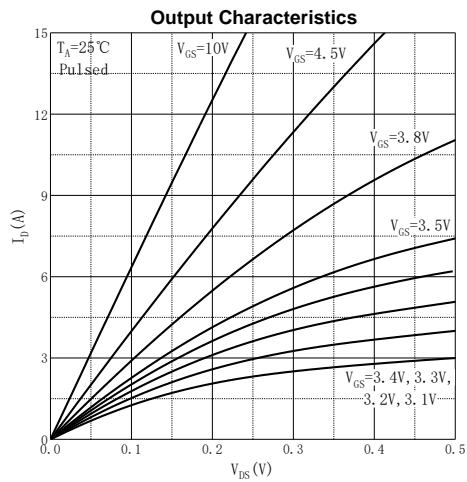
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

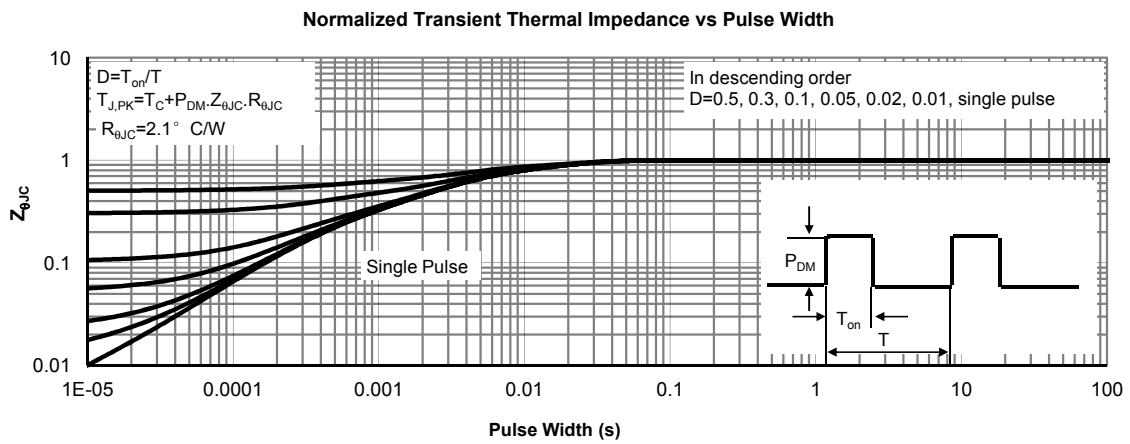
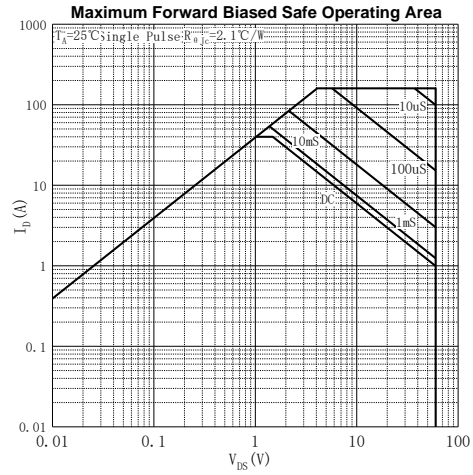
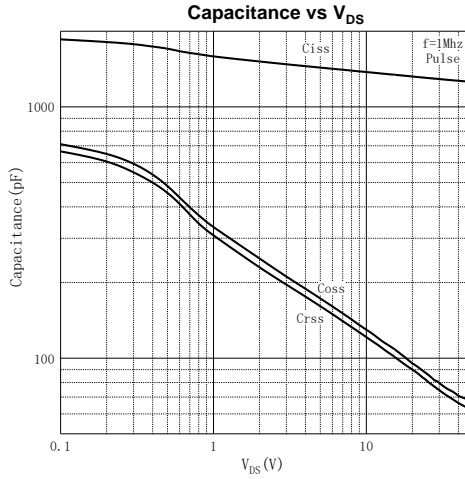
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.7	3	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		17	29	m $\Omega$
		$V_{GS} = 4.5V, I_D = 10A$		26	45	
Forward Transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 10A$	10			S
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 30V, V_{GS} = 0V, f = 1MHz$		1291		pF
Output Capacitance	$C_{oss}$			80		
Reverse Transfer Capacitance	$C_{rss}$			75		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.28		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 30V, V_{GS} = 10V, I_D = 10A$		28.5		nC
Gate-source Charge	$Q_{gs}$			7.6		
Gate-drain Charge	$Q_{gd}$			3.8		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 30V, V_{GS} = 10V, R_L = 1.5\Omega$ $R_G = 3\Omega$		8		ns
Turn-on Rise Time	$t_r$			5		
Turn-off Delay Time	$t_{d(off)}$			30		
Turn-off Fall Time	$t_f$			5.5		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.2	V

### Notes :

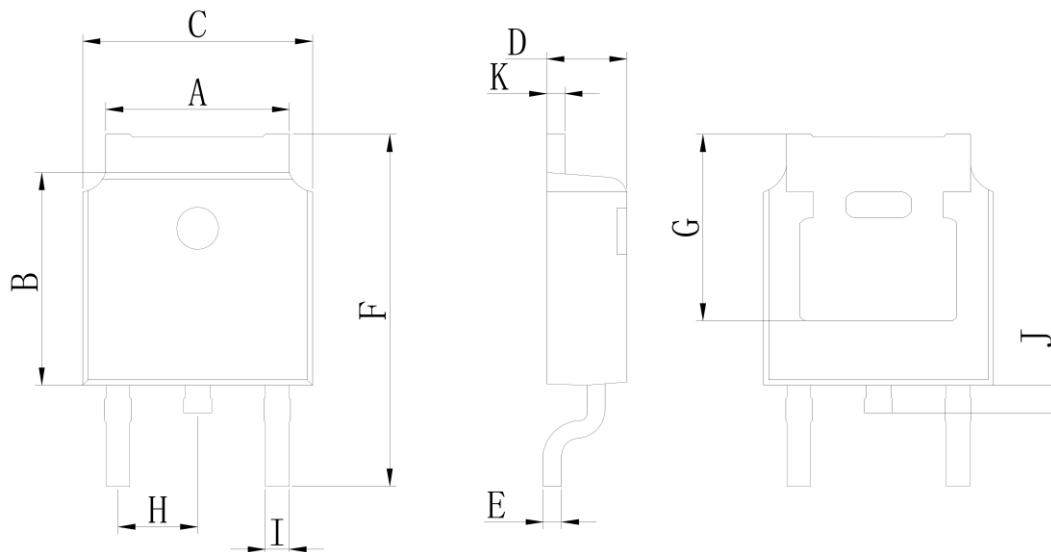
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.EAS condition:  $V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 6.Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## Typical Characteristics





## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	5.050	5.650	0.199	0.222
B	5.800	6.400	0.228	0.252
C	6.250	6.850	0.246	0.270
D	2.200	2.400	0.087	0.094
E	0.400	0.600	0.016	0.024
F	9.710	10.310	0.382	0.406
G	5.050	5.650	0.199	0.222
H	2.100	2.500	0.083	0.098
I	0.700	0.900	0.028	0.035
J	0.500	0.900	0.020	0.035
K	0.400	0.600	0.016	0.024